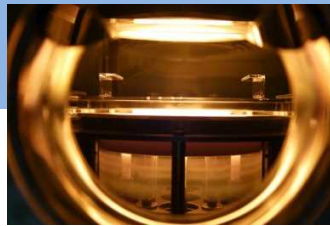
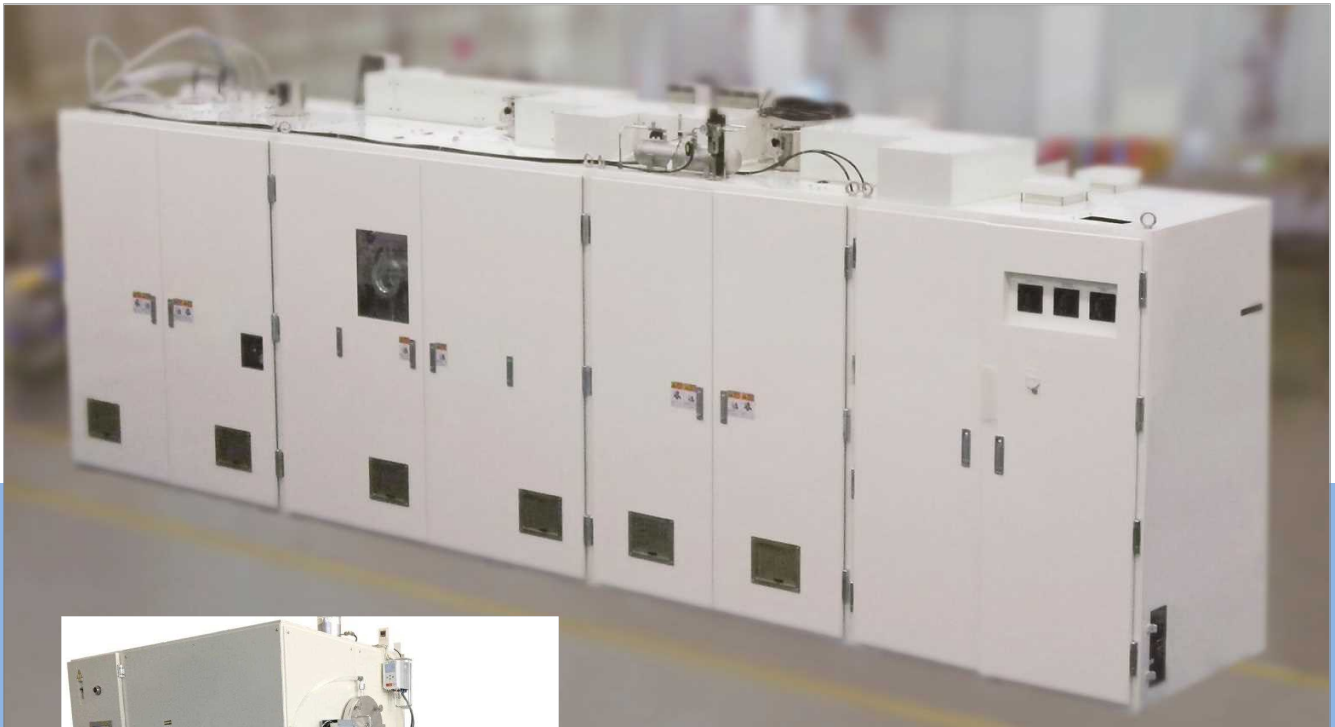




**TAIYO NIPPON SANSO**  
The Gas Professionals

# SR4000HT | High-Performance GaN MOCVD System with Annealing Reactor for AlN/AlGaIn Growth



## SR4000HT Specifications

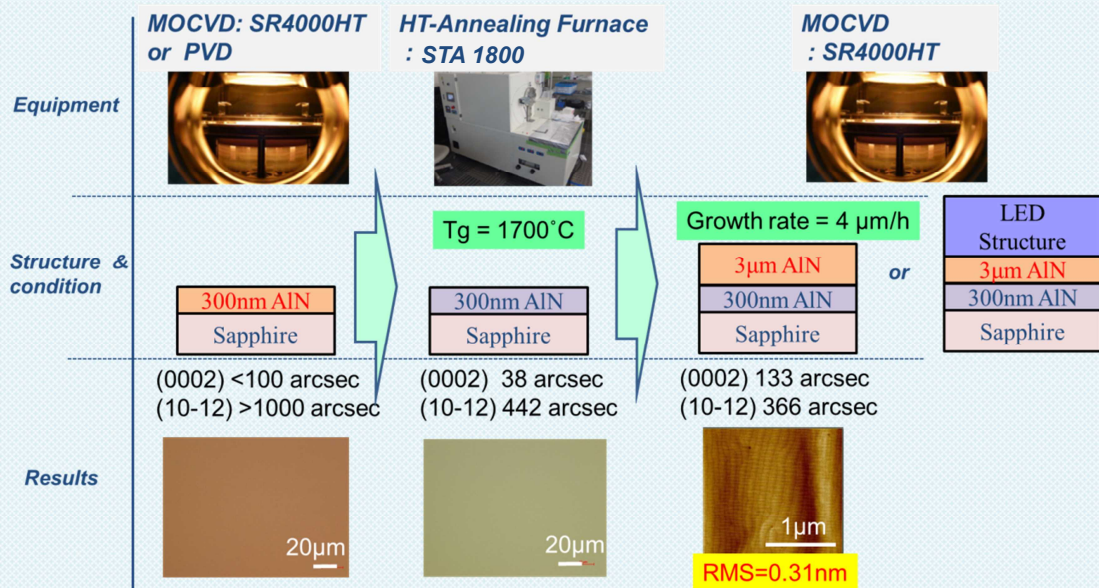
1. Wafer Size : 4" × 1, 2" × 3
2. Heating : up to **1350°C**
3. Growth at 10 kPa –100 kPa
4. 3-layer horizontal laminar flow

**High Quality AlN Growth**  
**Control of carbon concentration**  
**Control of gas phase reaction**

## Annealing Reactor Specifications

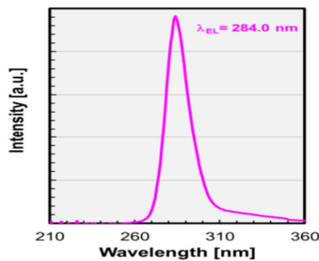
1. Wafer : 2" × max 32 pcs
2. Heating : up to **1800°C**

## 【Development of high-quality AlN buffer layer】



## 【Performance Of Light emitting device by SR4000HT】

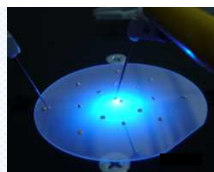
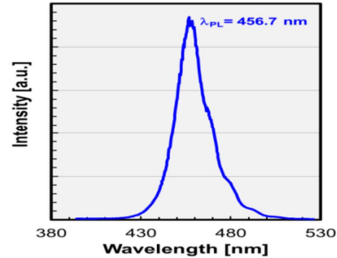
UV LED  
EL Spectrum



\*Collaboration with ITRI  
(Industrial Technology Research  
Institute of Taiwan)

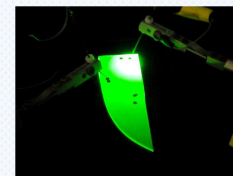
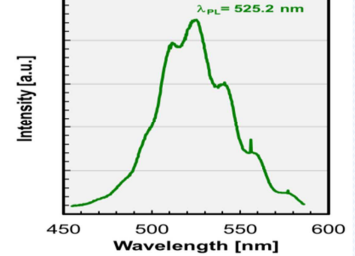
**IQE : 65%**  
30kPa Growth

Blue LED  
PL Spectrum



**IQE : 68%**  
Atmospheric  
(100kPa) growth

Green LED  
PL Spectrum



**IQE : 37%**  
Atmospheric  
(100kPa) growth

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